

Maximum Ratings (T = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (Gate Open, Sine Wave 50 to 60 Hz, $T_J = -40^{\circ}$ to 110°C)	V _{DRM} ,	600	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, T _c = 93°C)	I _{T (RMS)}	4.0	А
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T _C = 110°C)	I _{TSM}	40	А
Circuit Fusing Consideration (t = 8.3 msec)	l²t	6.6	A²sec
Peak Gate Current (Pulse Width \leq 20 μ sec, T_{C} = 108°C)	I _{GM}	4.0	А
Peak Gate Power (Pulse Width ≤ 10 μsec, T _C = 108°C)	P _{GM}	2.0	W
Peak Gate Voltage (Pulse Width ≤ 20 µsec, _c T= 93°C)	V _{GM}	5.0	V
Average Gate Power (t = 8.3 msec, T _C = 108°C)	P _{G(AV)}	1.0	W
Operating Junction Temperature Range	T _J	-40 to +110	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the

Thermal Characteristics

	Symbol	Value	Unit	
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient Junction-to-Ambient (Note 2)	Re _{JC} Re _{JA} Re _{JA}	3.5 88 80	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds		T _L	260	°C

^{2.} These ratings are applicable when surface mounted on the minimum pad sizes recommended.

Electrical Characteristics - **OFF** $(T_j = 25^{\circ}\text{C unless otherwise noted}; Electricals apply in both directions)$

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T ₁ = 25°C	I _{DRM} ,	-	-	0.01	m ^
$(V_D = V_{DRM} = V_{RRM}; Gate Open)$	$T_{J} = 110^{\circ}C$	I _{RRM}	-	-	2.0	mA

Electrical Characteristics - ON $(T_j = 25^{\circ}\text{C unless otherwise noted; Electricals apply in both directions)$

Charact	Symbol	Min	Тур	Max	Unit		
Peak On-State Voltage (Note 4) (I _{TM} = ±6.0 A)			V_{TM}	-	1.3	1.6	V
		MT2(+), G(+)		_	1.8	5.0	
Gate Trigger Current (Continuous dc)		MT2(+), G(-)		_	2.1	5.0	mA
$(V_D = 12 \text{ V}, \text{ R}_1 = 100 \Omega)$		MT2(-), G(-)	GT	_	2.4	5.0	IIIA
()		MT2(-), G(+)		_	4.2	10	
Holding Current (V _D = 12 V, Gate Open, Initiating	Current = ±200 mA))		I _H	-	1.5	15	mA
Gate Non-Trigger Voltage (Continuous dc) – ($V_D = 12 \text{ V}$, $R_L = 100 \Omega$, $T_J = 110^{\circ}\text{C}$) All Four Quadrants				0.1	0.4	-	V
	$(V_D = 12 \text{ V}, I_G = 5.0 \text{ mA})$	MT2(+), G(+)		-	1.75	10	mA
Latching Current	$(V_D = 12 \text{ V}, I_G = 5.0 \text{ mA})$	MT2(+), G(-)		-	5.2	10	
Laterling Current	$(V_D = 12 \text{ V}, I_G = 5.0 \text{ mA})$	MT2(-), G(-)	'L	-	2.1	10	
$(V_{\rm p} = 12 \text{V}, I_{\rm g} = 10 \text{mA})$		MT2(-), G(+)		-	2.2	10	
MT2(+), G(+)				0.5	0.62	1.3	
Gate Trigger Voltage (Continuous dc) $(V_D = 12 \text{ V}, R_1 = 100 \Omega)$		MT2(+), G(-)		0.5	0.57	1.3	V
		MT2(-), G(-)	V _{GT}	0.5	0.65	1.3	
	MT2(-), G(+)		0.5	0.74	1.3		

^{4.} Indicates Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.

Recommended Operating Conditions may affect device reliability.

1. V_{BBM} and V_{BBM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

^{3. 1/8&}quot; from case for 10 seconds.



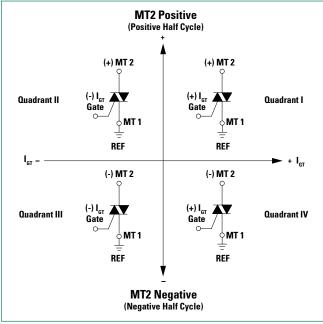
Dynamic Characteristics

Characteristic	Symbol	Min	Тур	Max	Unit
Rate of Change of Commutating Current ($V_D = 200 \text{ V}$, $I_{TM} = 1.8 \text{ A}$, Commutating dv/dt = 1.0 V/µsec, $I_J = 110^{\circ}\text{C}$,	(dl/dt)c	-	3.0	_	A/ms
Critical Rate of Rise of Off-State Voltage ($V_D = 0.67 \times V_{DRM}$, Exponential Waveform, Gate Open, $T_J = 110$ °C)	dV/dt	20	-	_	V/µs

Voltage Current Characteristic of SCR

Symbol	Parameter
V _{DRM}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Maximum On State Voltage
I _H	Holding Current

Quadrant Definitions for a Triac



All Polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used

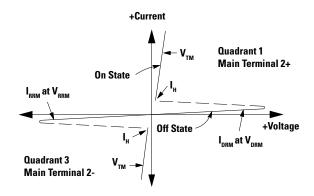




Figure 1. Typical RMS Current Derating

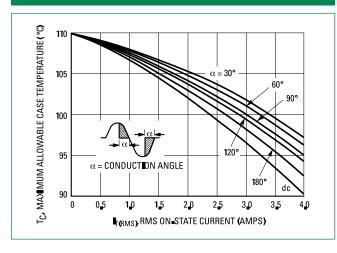


Figure 2. On-State Power Dissipation

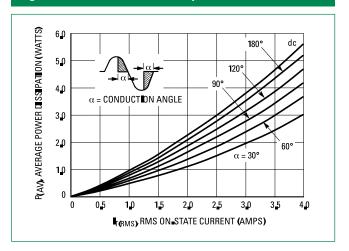


Figure 3. On-State Characteristics

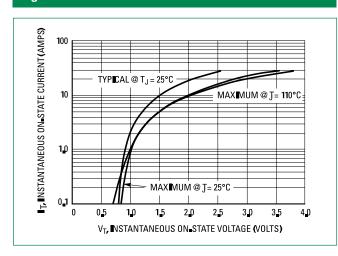


Figure 4. Transient Thermal Response

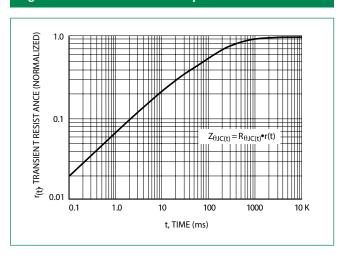


Figure 5. Typical Gate Trigger Current vs, Junction Temperature

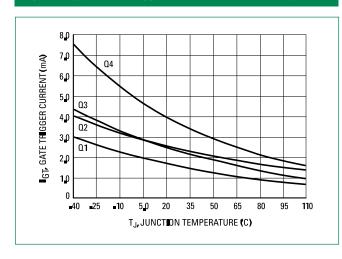


Figure 6. Typical Gate Trigger Voltage vs. Junction Temperature

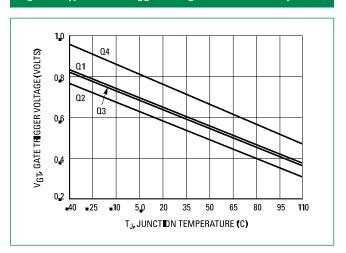




Figure 7. Typical Holding Current vs. Junction Temperature

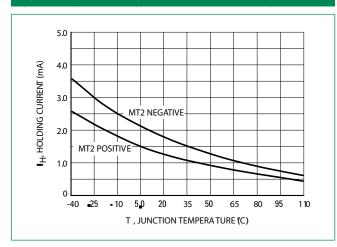


Figure 8. Typical Latching Current vs. Junction Temperature

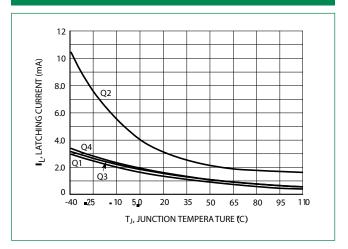


Figure 9. Exponential Static dv/dt vs.
Gate-MT1 Resistance, MT2(+)

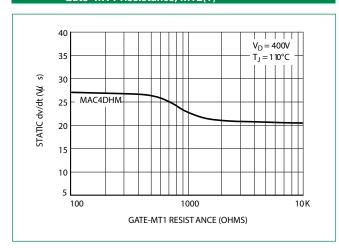


Figure 10. Exponential Static dv/dt vs. Gate-MT1 Resistance, MT2(-)

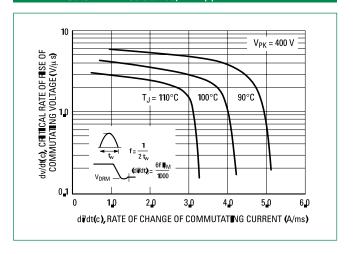
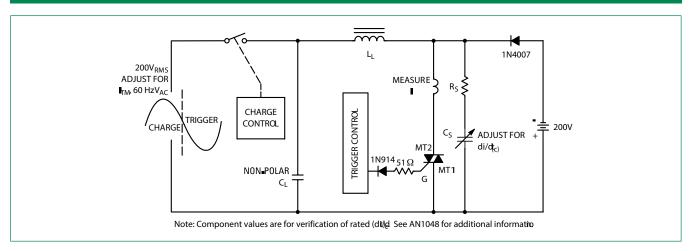
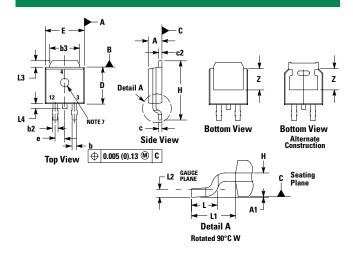


Figure 11. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)

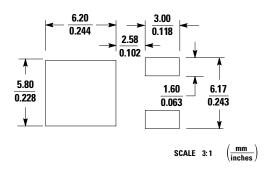




Dimensions



Soldering Footprint



Dim	Inches		Millin	neters
Dilli	Min	Max	Min	Max
Α	0.087	0.094	2.20	2.40
A1	0.000	0.005	0.00	0.12
b	0.022	0.030	0.55	0.75
b2	0.026	0.033	0.65	0.85
b3	0.209	0.217	5.30	5.50
С	0.019	0.023	0.49	0.59
c2	0.019	0.023	0.49	0.59
D	0.213	0.224	5.40	5.70
E	0.252	0.260	6.40	6.60
е	0.091		2.3	30
Н	0.374	0.406	9.50	10.30
L	0.058	0.070	1.47	1.78
L1	0.1	14	2.90	
L2	0.019	0.023	0.49	0.59
L3	0.053	0.065	1.35	1.65
L4	0.028	0.039	0.70	1.00
Z	0.154	-	3.90	-

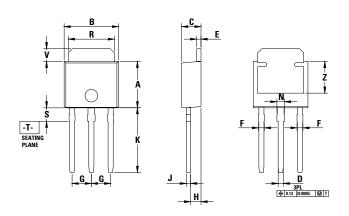
- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982.
 2. CONTROLLING DIMENSION: INCH. STYLE 6: PIN 1. MT1
 3. MT2
 4. GATE
 5. MT2



Dimensions

DPAK-3 Case 369D-01 Issue B

T0251-3L P0D



Dim	Inches		Millin	neters
Dim	Min	Max	Min	Max
Α	0.213	0.224	5.40	5.70
В	0.252	0.260	6.40	6.60
С	0.087	0.094	2.20	2.40
D	0.024	0.030	0.60	0.75
E	0.022	0.026	0.55	0.65
F	0.023	0.031	0.58	0.78
G	0.091	TYP.	2.30 TYP.	
Н	0.046	0.050	1.18	1.28
J	0.019	0.023	0.49	0.59
K	0.291	0.315	7.40	8.00
N	0.031	0.039	0.78	0.98
R	0.209	0.217	5.30	5.50
S	0.063 TYP.		1.60	TYP
V	0.053	0.065	1.35	1.65
Z	0.150	TYP.	3.80 TYP.	

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH. STYLE 6: PIN 1. MT1
 MT2
 ACATT

- GATE
 MT2

Part Marking System

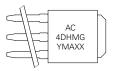


DPAK-3 Case 369C Style 6





DPAK-3 Case 369D Style 6



AC4DCx =Device Code x =D, M, or N X Y M A XX G =Year =Month =Assembly Site =Lot Serial Code =Pb-Free Package

Pin Assignment				
1	Main Terminal 1			
2	Main Terminal 2			
3	Gate			
4	Main Terminal 2			

Ordering Information

Device	Package Type	Package	Shipping
MAC4DHM-001	DPAK-3	369D	4000 Units / Box
MAC4DHM-001G	DPAK-3 (Pb-Free)	369D	4000 Units / Box
MAC4DHMT4	DPAK-3	369C	2500 / Tape & Reel
MAC4DHMT4G	DPAK-3 (Pb-Free)	369C	2500 / Tape & Reel

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